

PATENT ASSIGNMENT COVER SHEET

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SUBMISSION TYPE:	NEW ASSIGNMENT
NATURE OF CONVEYANCE:	ASSIGNMENT
CONVEYING PARTY DATA	
Name	Execution Date
NAGARJUNA INDUSTRIAL SERVICES AND INVESTMENTS PRIVATE LTD.	05/12/2016
RECEIVING PARTY DATA	
Name:	NAGARJUNA FERTILIZERS AND CHEMICALS LIMITED (NFCL)
Street Address:	D.NO.8-2-248, NAGARJUNA HILLS
Internal Address:	PUNJAGUTTA
City:	HYDERABAD, TELANGANA
State/Country:	INDIA
Postal Code:	500 082
PROPERTY NUMBERS Total: 2	
Property Type	Number
Patent Number:	8147656
Patent Number:	9382122
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NAME OF SUBMITTER:	FREDERICK J. DORCHAK
SIGNATURE:	/Frederick J. Dorchak/
DATE SIGNED:	07/12/2016
Total Attachments: 32	
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NAGARJUNA INDUSTRIAL SERVICES AND INVESTMENTS PRIVATE LTD

NAGARJUNA FERTILISERS AND CHEMICALS LIMITED

IP TRANSFER AGREEMENT

This IP TRANSFER AGREEMENT (the "Agreement") is made on May 12, 2016

BETWEEN

- (1) **Nagarjuna Industrial Services and Investments Private Ltd.**, registered in the commercial register of Mauritius under register number 094708, Suite G12, St. James Court, St. Denis Street, Port Louis, Mauritius ("**Nagarjuna Mauritius**"); and
- (2) **Nagarjuna Fertilizers and Chemicals Limited (NFCL)**, a Public Company Limited by Shares, registered under the Companies Act, 1956 with Corporate Identification number (CIN) L24129AP2006PLC076238, having its registered office at D.No.8-2-248, Nagarjuna Hills, Punjagutta, Hyderabad, Telangana – 500 082 ("**NFCL**"); Nagarjuna Mauritius and NFCL, together are called the "**Parties**".

WHEREAS

- (A) By purchase agreement dated 7 December 2009 (Notarial Deed No. 554/2009 BM of the notary Dr. Bernhard Meyding, Frankfurt am Main) Fnity PTE Ltd, a company registered in the register of companies of Singapore under register number 200107160G, 1 North Bridge Road #19-04/05, High Street Centre, 17094, Singapore ("**Fnity**"), acquired intellectual property rights, in particular patents and patent applications regarding polysilane technology, related documentation, receivables and claims (the "**Original IP**") from REV Renewable Energy Ventures Inc. and others (the "**IP Purchase Agreement**").
- (B) By undated IP sale and transfer agreement, **Spawnt Private S.à r.l.**, a Company registered in the commercial register of Luxembourg under register number R.C.S., Luxembourg B152.282, 7 Rue Robert Stümper, L-2557 Luxembourg ("**Spawnt Private**"); acquired the Original IP from Fnity (the "**Fnity Agreement**"). To the extent a transfer of the Original IP was not possible, Fnity granted transferable, sub-licensable, irrevocable, unrestricted licenses to Spawnt Private S.a.r.L (the "**Fnity Licenses**"; sections 2.2 and 2.3 of the Fnity Agreement). In addition, Fnity assigned all its warranty claims under the IP Purchase Agreement to Spawnt Private (the "**Warranty Claims**").
- (C) Spawnt Private was a shareholder of (i) Spawnt Research GmbH ("**Spawnt Research**") which was in charge of the research and development of polysilane related technology and (ii) Nagarjuna Spawnt GmbH which was in charge of the production and contribution of polysilane products. Spawnt Research and Nagarjuna Spawnt GmbH are insolvent at the date of this Agreement.
- (D) By research and development agreement between Spawnt Private and Spawnt Research dated 17 August 2010, Spawnt Private acquired all intellectual property rights of Spawnt Research, in particular all rights regarding inventions made and claimed by Spawnt Research in view of its research activities in the field of polysilanes, and related documentation and claims; Spawnt Private directly applied for patents based on such inventions in its own name (the "**New IP**"). The New IP and the Original IP together are called the "**Spawnt IP**".
- (E) By IP sale and transfer agreement dated March 24, 2016, Nagarjuna Mauritius acquired the Spawnt IP from Spawnt Private (the "**Spawnt Agreement**").

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- (F) By way of this Agreement, NFCL wishes to acquire and Nagarjuna Mauritius wishes to transfer to NFCL the Spawnt IP without any limitation. Nagarjuna Mauritius, Spawnt Private and Fnity wish to cancel the Fnity Licenses in order to put Fnity into the position to grant such licenses to NFCL.

THEREFORE, the parties agree the following:

1. TRANSFER AND ASSIGNMENT OF THE SPAWNT IP

1.1 Nagarjuna Mauritius is obliged to transfer and to assign and hereby transfers and assigns the Spawnt IP and all rights in and title and ownership to the Spawnt IP to NFCL. This transfer includes but is not limited to the patents and patent applications listed in Annex I to this Agreement.

1.2 NFCL accepts the transfer and assignment.

2. DECLARATION OF TRANSFER

2.1 Nagarjuna Mauritius hereby agrees to any registration (i) of the transfer of ownership and (ii) of NFCL as the new owner of the Spawnt IP. Nagarjuna Mauritius shall make any declaration necessary for the registration of NFCL as the new owner of the Spawnt IP, in particular in view of the patents and patent applications listed in Annex I.

2.2 For the purpose to enforce, exercise, complete, and register the transfer of ownership, Nagarjuna Mauritius hereby grants NFCL power of attorney. NFCL is authorized to represent Nagarjuna Mauritius, in particular to make declarations in the name of Nagarjuna Mauritius vis-à-vis patent offices. NFCL is exempted from any potential restrictions under the relevant laws, such as restrictions regarding self-dealing.

2.3 A separate copy of NFCL power of attorney is attached to this IP Transfer Agreement as Annex 2.

3. HAND OVER OF DOCUMENTATION

Nagarjuna Mauritius shall hand over to NFCL any documentation related to the Spawnt IP, in particular the documentation of patents and regarding the assignment of invention rights.

4. ASSIGNMENT OF THE WARRANTY CLAIMS

Nagarjuna Mauritius is obliged to assign and hereby assigns the Warranty Claims to NFCL. NFCL accepts the assignment.

5. **CANCELLATION OF THE FNITY LICENSES**

Nagarjuna Mauritius agree that the Fnity Licenses are cancelled upon signing of this Agreement.

6. **BACK-UP TRANSFER AND LICENSE TO NAGARJUNA MAURITIUS**

6.1 To the extent that the transfer and assignment of the Original IP from Fnity to Spawnt Private under the Fnity Agreement was not permissible under applicable laws, Nagarjuna Mauritius agrees to procure from Fnity transfers and assignments of the Original IP and all rights in and title and ownership to the Original IP to NFCL. To the extent such transfer is not permissible under applicable laws, such rights shall be held in trust for and on behalf of Nagarjuna Mauritius and hereby grants an exclusive, transferrable, sub-licensable, irrevocable, unrestricted, and royalty-free license to use and exploit the Original IP to NFCL.

6.2 To the extent the transfer and assignment of the Original IP under the IP Purchase Agreement was not permissible under applicable laws and to the extent that as a consequence of this, Fnity only holds an exclusive, transferrable, sub-licensable, irrevocable, unrestricted and royalty-free license to use the Original IP, Nagarjuna Mauritius agrees to procure from Fnity transferable, sub-licensable, irrevocable, unrestricted, and royalty-free sub-license to use and exploit the Original IP to NFCL.

7. **CONSIDERATION**

7.1 In consideration of the transfer of the Spawnt IP, NFCL pays to Nagarjuna Mauritius EUR 65,000 (the "Payment").

7.2 NFCL has from time to time at the request of Nagarjuna Mauritius provided loans.

7.3 As on date the total loan outstanding is EURO 4,275,000.

7.4 Nagarjuna Mauritius requests NFCL to adjust EURO 65,000 from out of the loan provided and payable to NFCL towards the consideration for sale of patents.

7.5 Nagarjuna Mauritius confirms having received consideration of Euro 65,000 as on May 12, 2016

7.6 Except the consideration, there is no other payment or compensation obligation between the Parties.

8. **LIABILITY**

In consideration of the assignment of the Warranty Claims any liability of Nagarjuna Mauritius, Spawnt Private or Fnity for defects in title (*Rechtsmängel*) or in quality

(Sachmängel) regarding the Spawnt IP shall be excluded to the extent permitted by law.

9. **EFFECTIVE DATE**

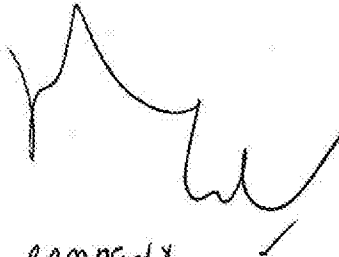
The Effective Date of the Agreement shall be the date May 12, 2016

10. **FINAL PROVISIONS**

10.1 Should a provision of this Agreement or a provision later on included in this Agreement be or become null and void as a whole or in part, or should a gap in this Agreement become evident, this does not affect the validity of the remaining provisions.

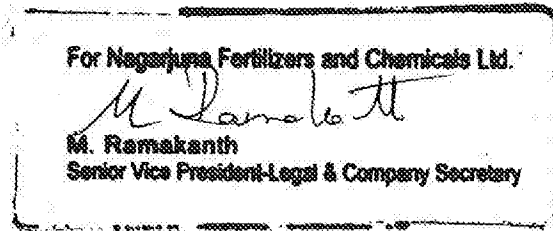
10.2 The agreements stipulated herein between Spawnt Private and Nagarjuna Mauritius can be changed, terminated, or amended by the affected parties.

10.3 This Agreement shall be governed by the laws of India,



V. RAMDANI

for an on behalf of Nagarjuna Industrial Services and Investments Private Ltd.



For Nagarjuna Fertilizers and Chemicals Ltd.
M. Ramakanth
Senior Vice President-Legal & Company Secretary

for and on behalf of Nagarjuna Fertilizers and Chemicals Limited

Annex I

List of Patents

S. No	Reference	Country	Application / Publication / Patent Number	Abstract
1	TT0004	AT	E410396	The present invention relates to a method for the production of silicon from silyl halides. In a first step, the silyl halide is converted, with the generation of a plasma discharge, to a halogenated polysilane, which is subsequently decomposed to silicon
2	TT0004	CN	ZL200680017874.1	The present invention relates to a method for the production of silicon from silyl halides. In a first step, the silyl halide is converted, with the generation of a plasma discharge, to a halogenated polysilane, which is subsequently decomposed to silicon
3	TT0004	DE	102005024041.00	The present invention relates to a method for the production of silicon from silyl halides. In a first step, the silyl halide is converted, with the generation of a plasma discharge, to a halogenated polysilane, which is subsequently decomposed to silicon
4	TT0004	DE	502006001783.0	The present invention relates to a method for the production of silicon from silyl halides. In a first step, the silyl halide is converted, with the generation of a plasma discharge, to a halogenated polysilane, which is subsequently decomposed to silicon
5	TT0004	FR	1896362	The present invention relates to a method for the production of silicon from silyl halides. In a first step, the silyl halide is converted, with the generation of a plasma discharge, to a halogenated polysilane, which is subsequently decomposed to silicon
6	TT0004	GB	1896362	The present invention relates to a method for the production of silicon from silyl halides. In a first step, the silyl halide is converted, with the generation of a plasma discharge, to a halogenated polysilane, which is subsequently decomposed to silicon
7	TT0004	IT	19070BE/2009	The present invention relates to a method for the production of silicon from silyl halides. In a first step, the silyl halide is converted, with the generation of a plasma discharge, to a halogenated polysilane, which is subsequently decomposed to silicon
8	TT0004	JP	4832511	The present invention relates to a method for the production of silicon from silyl halides. In a first step, the silyl halide is converted, with the generation of a plasma discharge, to a halogenated polysilane, which is subsequently decomposed to silicon
9	TT0004	US	8,147,656	The present invention relates to a method for the production of silicon from silyl halides. In a first step, the silyl halide is converted, with the generation of a plasma discharge, to a halogenated polysilane, which is subsequently decomposed to silicon
11	TT0005	DE	102005053781	Hydrogen generation for operating fuel cells, comprises reacting silicon and/or a silicon-containing alloy with an alkaline solution as catalyst, in a reaction vessel (1) to form silicon dioxide as nucleator, and depositing the formed silicon dioxide on c
12	TT0005	DE	102006020786	Hydrogen generation for operating fuel cells, comprises reacting silicon and/or a silicon-containing alloy with an alkaline solution as catalyst, in a reaction vessel (1) to form silicon dioxide as nucleator, and depositing the formed silicon dioxide on c

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13	TT0005	EP	6818429.00	Hydrogen generation for operating fuel cells, comprises reacting silicon and/or a silicon-containing alloy with an alkaline solution as catalyst, in a reaction vessel (1) to form silicon dioxide as nucleator, and depositing the formed silicon dioxide on c
14	TT0006	AU	2007276384	The invention relates to a method for the final product-related manufacture of low-molecular, medium-molecular, and high-molecular halogenated polysilanes, the distillation thereof into selected fractions, the direct deposition of silicon from the gas pha
15	TT0006	AU	2013224703.00	The invention relates to a method for the final product-related manufacture of low-molecular, medium-molecular, and high-molecular halogenated polysilanes, the distillation thereof into selected fractions, the direct deposition of silicon from the gas pha
16	TT0006	CN	ZL200780030815.2	The invention relates to a method for the final product-related manufacture of low-molecular, medium-molecular, and high-molecular halogenated polysilanes, the distillation thereof into selected fractions, the direct deposition of silicon from the gas pha
17	TT0006	DE	102006034061.20	The invention relates to a method for the final product-related manufacture of low-molecular, medium-molecular, and high-molecular halogenated polysilanes, the distillation thereof into selected fractions, the direct deposition of silicon from the gas pha
18	TT0006	EP	11167143.40	The invention relates to a method for the final product-related manufacture of low-molecular, medium-molecular, and high-molecular halogenated polysilanes, the distillation thereof into selected fractions, the direct deposition of silicon from the gas pha
19	TT0006	EP	2361945	The invention relates to a method for the final product-related manufacture of low-molecular, medium-molecular, and high-molecular halogenated polysilanes, the distillation thereof into selected fractions, the direct deposition of silicon from the gas pha
20	TT0006	EP	2361946	The invention relates to a method for the final product-related manufacture of low-molecular, medium-molecular, and high-molecular halogenated polysilanes, the distillation thereof into selected fractions, the direct deposition of silicon from the gas pha
21	TT0006	EP	2361943	The invention relates to a method for the final product-related manufacture of low-molecular, medium-molecular, and high-molecular halogenated polysilanes, the distillation thereof into selected fractions, the direct deposition of silicon from the gas pha
22	TT0006	EP	2044143	The invention relates to a method for the final product-related manufacture of low-molecular, medium-molecular, and high-molecular halogenated polysilanes, the distillation thereof into selected fractions, the direct deposition of silicon from the gas pha
23	TT0006	JP	5520602	The invention relates to a method for the final product-related manufacture of low-molecular, medium-molecular, and high-molecular halogenated polysilanes, the distillation thereof into selected fractions, the direct deposition of silicon from the gas pha
24	TT0007	AT	E508.983	The invention relates to a process for preparing hydrogen. According to the invention, monosilane or polysilane is converted to hydrogen at an elevated temperature with steam or oxygen.
25	TT0007	CN	101573288.00	The invention relates to a process for preparing hydrogen. According to the invention, monosilane or polysilane is converted to hydrogen at an elevated temperature with steam or oxygen.
26	TT0007	DE	502007007189.7	The invention relates to a process for preparing hydrogen. According to the invention, monosilane or polysilane is converted to hydrogen at an elevated temperature with steam or oxygen.

27	TT0007	ES	2043949	The invention relates to a process for preparing hydrogen. According to the invention, monosilane or polysilane is converted to hydrogen at an elevated temperature with steam or oxygen.
28	TT0007	FR	2043949	The invention relates to a process for preparing hydrogen. According to the invention, monosilane or polysilane is converted to hydrogen at an elevated temperature with steam or oxygen.
29	TT0007	GB	2043949	The invention relates to a process for preparing hydrogen. According to the invention, monosilane or polysilane is converted to hydrogen at an elevated temperature with steam or oxygen.
30	TT0007	IN	239/KOLNP/2009	The invention relates to a process for preparing hydrogen. According to the invention, monosilane or polysilane is converted to hydrogen at an elevated temperature with steam or oxygen.
31	TT0007	IT	2043949	The invention relates to a process for preparing hydrogen. According to the invention, monosilane or polysilane is converted to hydrogen at an elevated temperature with steam or oxygen.
32	TT0007	JP	5249216	The invention relates to a process for preparing hydrogen. According to the invention, monosilane or polysilane is converted to hydrogen at an elevated temperature with steam or oxygen.
33	TT0007	US	8,414,863	The invention relates to a process for preparing hydrogen. According to the invention, monosilane or polysilane is converted to hydrogen at an elevated temperature with steam or oxygen.
34	TT0008	CN	ZL200780029023.3	Process for supplying a fuel cell with hydrogen, which includes the steps:-intermediate storage of (poly)silanes or (poly)silane solutions-transfer of the (poly)silanes to a reaction chamber-reaction or hydrolysis of the silanes or silane solutions in the
35	TT0008	EP	2047552.00	Process for supplying a fuel cell with hydrogen, which includes the steps:-intermediate storage of (poly)silanes or (poly)silane solutions-transfer of the (poly)silanes to a reaction chamber-reaction or hydrolysis of the silanes or silane solutions in the
36	TT0008	IN	434/KOLNP/2009	Process for supplying a fuel cell with hydrogen, which includes the steps:-intermediate storage of (poly)silanes or (poly)silane solutions-transfer of the (poly)silanes to a reaction chamber-reaction or hydrolysis of the silanes or silane solutions in the
37	TT0008	JP	5448815	Process for supplying a fuel cell with hydrogen, which includes the steps:-intermediate storage of (poly)silanes or (poly)silane solutions-transfer of the (poly)silanes to a reaction chamber-reaction or hydrolysis of the silanes or silane solutions in the
38	TT0008	US	8,435,476	Process for supplying a fuel cell with hydrogen, which includes the steps:-intermediate storage of (poly)silanes or (poly)silane solutions-transfer of the (poly)silanes to a reaction chamber-reaction or hydrolysis of the silanes or silane solutions in the
39	TT0008	US	13/848,573	Process for supplying a fuel cell with hydrogen, which includes the steps:-intermediate storage of (poly)silanes or (poly)silane solutions-transfer of the (poly)silanes to a reaction chamber-reaction or hydrolysis of the silanes or silane solutions in the
40	TT0009	DE	102006043929	The invention is directed to mixtures of polysilanes macroscopically solid at ambient temperature wherein the individual components of the composition Si_nH_{2n} and/or $\text{Si}_n\text{H}_{2n+2}$ of which decompose before they are boiling at an applied process pressure and whi
41	TT0009	EP	2064267	The invention is directed to mixtures of polysilanes macroscopically solid at ambient temperature wherein the individual components of the composition Si_nH_{2n} and/or $\text{Si}_n\text{H}_{2n+2}$ of which decompose before they are boiling at an applied process pressure and whi
42	TT0009	US	8,177,943	The invention is directed to mixtures of polysilanes macroscopically solid at ambient temperature wherein the individual components of the composition Si_nH_{2n} and/or $\text{Si}_n\text{H}_{2n+2}$ of which decompose before they are boiling at an applied process pressure and whi
43	TT0013	DE	102007013219	The invention is based on the aim of developing a device and a method for the plasma-enhanced synthesis of halogenated polysilanes and polygermanes, where in at least one reaction

				partner is present in a gaseous form and is excited by reactive particles fr
44	TT0013	EP	2137236	The invention is based on the aim of developing a device and a method for the plasma-enhanced synthesis of halogenated polysilanes and polygermanes, wherein at least one reaction partner is present in a gaseous form and is excited by reactive particles fr
45	TT0013	IN	1931/MUMNP/2009	The invention is based on the aim of developing a device and a method for the plasma-enhanced synthesis of halogenated polysilanes and polygermanes, wherein at least one reaction partner is present in a gaseous form and is excited by reactive particles fr
46	TT0013	JP	5415290	The invention is based on the aim of developing a device and a method for the plasma-enhanced synthesis of halogenated polysilanes and polygermanes, wherein at least one reaction partner is present in a gaseous form and is excited by reactive particles fr
47	TT0013	KR	10-2009-7021530	The invention is based on the aim of developing a device and a method for the plasma-enhanced synthesis of halogenated polysilanes and polygermanes, wherein at least one reaction partner is present in a gaseous form and is excited by reactive particles fr
48	TT0013	US	12/530,662	The invention is based on the aim of developing a device and a method for the plasma-enhanced synthesis of halogenated polysilanes and polygermanes, wherein at least one reaction partner is present in a gaseous form and is excited by reactive particles fr
49	TT0014	AT	E508.985	The invention relates to a method for the catalytic hydrogenation of halogenated silanes or halogenated germanes, according to which halogenated monosilanes, oligosilanes or polysilanes, or monogermanes, oligogermanes or polygermanes, are hydrogenated or
50	TT0014	CN	ZL200880018321.7	The invention relates to a method for the catalytic hydrogenation of halogenated silanes or halogenated germanes, according to which halogenated monosilanes, oligosilanes or polysilanes, or monogermanes, oligogermanes or polygermanes, are hydrogenated or
51	TT0014	DE	502008003497.8	The invention relates to a method for the catalytic hydrogenation of halogenated silanes or halogenated germanes, according to which halogenated monosilanes, oligosilanes or polysilanes, or monogermanes, oligogermanes or polygermanes, are hydrogenated or
52	TT0014	ES	2366597	The invention relates to a method for the catalytic hydrogenation of halogenated silanes or halogenated germanes, according to which halogenated monosilanes, oligosilanes or polysilanes, or monogermanes, oligogermanes or polygermanes, are hydrogenated or
53	TT0014	FR	2132137	The invention relates to a method for the catalytic hydrogenation of halogenated silanes or halogenated germanes, according to which halogenated monosilanes, oligosilanes or polysilanes, or monogermanes, oligogermanes or polygermanes, are hydrogenated or
54	TT0014	GB	2132137	The invention relates to a method for the catalytic hydrogenation of halogenated silanes or halogenated germanes, according to which halogenated monosilanes, oligosilanes or polysilanes, or monogermanes, oligogermanes or polygermanes, are hydrogenated or
55	TT0014	IN	264800	The invention relates to a method for the catalytic hydrogenation of halogenated silanes or halogenated germanes, according to which halogenated monosilanes, oligosilanes or polysilanes, or monogermanes, oligogermanes or polygermanes, are hydrogenated or

56	TT0014	IT	2132137	The invention relates to a method for the catalytic hydrogenation of halogenated silanes or halogenated germanes, according to which halogenated monosilanes, oligosilanes or polysilanes, or monogermanes, oligogermanes or polygermanes, are hydrogenated or
57	TT0014	KR	10-2009-7022832	The invention relates to a method for the catalytic hydrogenation of halogenated silanes or halogenated germanes, according to which halogenated monosilanes, oligosilanes or polysilanes, or monogermanes, oligogermanes or polygermanes, are hydrogenated or
58	TT0014	US	8,372,370	The invention relates to a method for the catalytic hydrogenation of halogenated silanes or halogenated germanes, according to which halogenated monosilanes, oligosilanes or polysilanes, or monogermanes, oligogermanes or polygermanes, are hydrogenated or
59	TT0015	CN	ZL200880018219.7	The invention relates to a method for the plasma-assisted synthesis of organohalosilanes in which organohalosilanes of the general empirical formula $R_1mR_2oS_iX_4-p$ ($X=F, Cl, Br$ or I ; $p=1-4$; $p=m+o$; $m=1-4$; $o=0-3$; $R_1, R_2 =$ alkyl, alkenyl, alkynyl, aryl) and/
60	TT0015	DE	502008008109.7	The invention relates to a method for the plasma-assisted synthesis of organohalosilanes in which organohalosilanes of the general empirical formula $R_1mR_2oS_iX_4-p$ ($X=F, Cl, Br$ or I ; $p=1-4$; $p=m+o$; $m=1-4$; $o=0-3$; $R_1, R_2 =$ alkyl, alkenyl, alkynyl, aryl) and/
61	TT0015	ES	2142557	The invention relates to a method for the plasma-assisted synthesis of organohalosilanes in which organohalosilanes of the general empirical formula $R_1mR_2oS_iX_4-p$ ($X=F, Cl, Br$ or I ; $p=1-4$; $p=m+o$; $m=1-4$; $o=0-3$; $R_1, R_2 =$ alkyl, alkenyl, alkynyl, aryl) and/
62	TT0015	FR	2142557	The invention relates to a method for the plasma-assisted synthesis of organohalosilanes in which organohalosilanes of the general empirical formula $R_1mR_2oS_iX_4-p$ ($X=F, Cl, Br$ or I ; $p=1-4$; $p=m+o$; $m=1-4$; $o=0-3$; $R_1, R_2 =$ alkyl, alkenyl, alkynyl, aryl) and/
63	TT0015	GB	2142557	The invention relates to a method for the plasma-assisted synthesis of organohalosilanes in which organohalosilanes of the general empirical formula $R_1mR_2oS_iX_4-p$ ($X=F, Cl, Br$ or I ; $p=1-4$; $p=m+o$; $m=1-4$; $o=0-3$; $R_1, R_2 =$ alkyl, alkenyl, alkynyl, aryl) and/
64	TT0015	IN	2032/MUMNP/2009	The invention relates to a method for the plasma-assisted synthesis of organohalosilanes in which organohalosilanes of the general empirical formula $R_1mR_2oS_iX_4-p$ ($X=F, Cl, Br$ or I ; $p=1-4$; $p=m+o$; $m=1-4$; $o=0-3$; $R_1, R_2 =$ alkyl, alkenyl, alkynyl, aryl) and/
65	TT0015	IT	2142557	The invention relates to a method for the plasma-assisted synthesis of organohalosilanes in which organohalosilanes of the general empirical formula $R_1mR_2oS_iX_4-p$ ($X=F, Cl, Br$ or I ; $p=1-4$; $p=m+o$; $m=1-4$; $o=0-3$; $R_1, R_2 =$ alkyl, alkenyl, alkynyl, aryl) and/
66	TT0015	US	2011-0132744	The invention relates to a method for the plasma-assisted synthesis of organohalosilanes in which organohalosilanes of the general empirical formula $R_1mR_2oS_iX_4-p$ ($X=F, Cl, Br$ or I ; $p=1-4$; $p=m+o$; $m=1-4$; $o=0-3$; $R_1, R_2 =$ alkyl, alkenyl, alkynyl, aryl) and/
67	TT0020	AU	2009253523	The invention relates to a halogenated polysilane (referred to in the following as polysilane) as a pure compound or as a mixture of compounds and to a thermal process for producing the same. The polysilane is characterized by characteristic shifts in its
68	TT0020	CA	2,725,366	The invention relates to a halogenated polysilane (referred to in the following as polysilane) as a pure compound or as a mixture of compounds and to a thermal process for producing the same. The polysilane is characterized by characteristic shifts in its
69	TT0020	CN	ZL200980119335.2	The invention relates to a halogenated polysilane (referred to in the following as polysilane) as a pure compound or as a mixture of compounds and to a thermal process for producing the same.

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				The polysilane is characterized by characteristic shifts in its
70	TT0020	DE	102008025260	The invention relates to a halogenated polysilane (referred to in the following as polysilane) as a pure compound or as a mixture of compounds and to a thermal process for producing the same. The polysilane is characterized by characteristic shifts in its
71	TT0020	DE	502009008986.4	The invention relates to a halogenated polysilane (referred to in the following as polysilane) as a pure compound or as a mixture of compounds and to a thermal process for producing the same. The polysilane is characterized by characteristic shifts in its
72	TT0020	EP	2296804	The invention relates to a halogenated polysilane (referred to in the following as polysilane) as a pure compound or as a mixture of compounds and to a thermal process for producing the same. The polysilane is characterized by characteristic shifts in its
73	TT0020	FR	2296804	The invention relates to a halogenated polysilane (referred to in the following as polysilane) as a pure compound or as a mixture of compounds and to a thermal process for producing the same. The polysilane is characterized by characteristic shifts in its
74	TT0020	GB	2296804	The invention relates to a halogenated polysilane (referred to in the following as polysilane) as a pure compound or as a mixture of compounds and to a thermal process for producing the same. The polysilane is characterized by characteristic shifts in its
75	TT0020	IN	4489/KOLNP/2010	The invention relates to a halogenated polysilane (referred to in the following as polysilane) as a pure compound or as a mixture of compounds and to a thermal process for producing the same. The polysilane is characterized by characteristic shifts in its
76	TT0020	JP	5639047	The invention relates to a halogenated polysilane (referred to in the following as polysilane) as a pure compound or as a mixture of compounds and to a thermal process for producing the same. The polysilane is characterized by characteristic shifts in its
77	TT0020	KR	10-2010-7029330	The invention relates to a halogenated polysilane (referred to in the following as polysilane) as a pure compound or as a mixture of compounds and to a thermal process for producing the same. The polysilane is characterized by characteristic shifts in its
78	TT0020	US	12/995,174	The invention relates to a halogenated polysilane (referred to in the following as polysilane) as a pure compound or as a mixture of compounds and to a thermal process for producing the same. The polysilane is characterized by characteristic shifts in its
79	TT0021	AU	2009253522	The invention relates to a halogenated polysilane (referred to in the following as polysilane) as a pure compound or as a mixture of compounds and to a plasma-chemical process for producing the same. The polysilane is particularly soluble and fusible and
80	TT0021	CA	2,726,000	The invention relates to a halogenated polysilane (referred to in the following as polysilane) as a pure compound or as a mixture of compounds and to a plasma-chemical process for producing the same. The polysilane is particularly soluble and fusible and
81	TT0021	DE	502009007550.2	The invention relates to a halogenated polysilane (referred to in the following as polysilane) as a pure compound or as a mixture of compounds and to a plasma-chemical process for producing the same. The polysilane is particularly soluble and fusible and
82	TT0021	DE	102008025261	The invention relates to a halogenated polysilane (referred to in the following as polysilane) as a pure compound or as a mixture of compounds and to a plasma-chemical process for producing the same. The polysilane is particularly soluble and fusible and
83	TT0021	EP	2296803	The invention relates to a halogenated polysilane (referred to in the following as polysilane) as a pure compound or as a mixture of compounds and to a plasma-chemical process for producing the same. The polysilane is particularly soluble and fusible and
84	TT0021	FR	2296803	The invention relates to a halogenated polysilane (referred to in the following as polysilane) as a pure compound or as a mixture of compounds and to a plasma-chemical process for producing the same. The polysilane is particularly soluble and fusible and

85	TT0021	GB	2296803	The invention relates to a halogenated polysilane (referred to in the following as polysilane) as a pure compound or as a mixture of compounds and to a plasma-chemical process for producing the same. The polysilane is particularly soluble and fusible and
86	TT0021	IN	4503/KOLNP/2010	The invention relates to a halogenated polysilane (referred to in the following as polysilane) as a pure compound or as a mixture of compounds and to a plasma-chemical process for producing the same. The polysilane is particularly soluble and fusible and
87	TT0021	JP	5658143	The invention relates to a halogenated polysilane (referred to in the following as polysilane) as a pure compound or as a mixture of compounds and to a plasma-chemical process for producing the same. The polysilane is particularly soluble and fusible and
88	TT0021	KR	10-2010-7029329	The invention relates to a halogenated polysilane (referred to in the following as polysilane) as a pure compound or as a mixture of compounds and to a plasma-chemical process for producing the same. The polysilane is particularly soluble and fusible and
89	TT0021	US	12/995,173	The invention relates to a halogenated polysilane (referred to in the following as polysilane) as a pure compound or as a mixture of compounds and to a plasma-chemical process for producing the same. The polysilane is particularly soluble and fusible and
90	TT0022/0023	DE	502009010066.3	The invention relates to silicon containing halogenide obtained by thermal disintegration of halogenized polysilane, and a method for producing the silicon. The silicon has a halogenide content of 1 at%-50 at%. The invention further relates to the use of
91	TT0022/0023	DE	102008025263	The invention relates to silicon containing halogenide obtained by thermal disintegration of halogenized polysilane, and a method for producing the silicon. The silicon has a halogenide content of 1 at%-50 at%. The invention further relates to the use of
92	TT0022/0023	FR	2300368	The invention relates to silicon containing halogenide obtained by thermal disintegration of halogenized polysilane, and a method for producing the silicon. The silicon has a halogenide content of 1 at%-50 at%. The invention further relates to the use of
93	TT0022/0023	GB	2300368	The invention relates to silicon containing halogenide obtained by thermal disintegration of halogenized polysilane, and a method for producing the silicon. The silicon has a halogenide content of 1 at%-50 at%. The invention further relates to the use of
94	TT0022/0023	IN	4989/KOLNP/2010	The invention relates to silicon containing halogenide obtained by thermal disintegration of halogenized polysilane, and a method for producing the silicon. The silicon has a halogenide content of 1 at%-50 at%. The invention further relates to the use of
95	TT0022/0023	KR	10-2010-7029324	The invention relates to silicon containing halogenide obtained by thermal disintegration of halogenized polysilane, and a method for producing the silicon. The silicon has a halogenide content of 1 at%-50 at%. The invention further relates to the use of
96	TT0029	EP	09771469.5	The invention describes a process for removing nonmetallic impurities from metallurgical silicon. A melt is produced from metallurgical silicon and halide-containing silicon. As a result, the impurities are sublimed out and removed from the melt in the fo
97	TT0029	EP	09771469.5	The invention describes a process for removing nonmetallic impurities from metallurgical silicon. A melt is produced from metallurgical silicon and halide-containing silicon. As a result, the impurities are sublimed out and removed from the melt in the fo
98	TT0029	IN	565/KOLNP/2011	The invention describes a process for removing nonmetallic impurities from metallurgical silicon. A melt is produced from metallurgical silicon and halide-containing silicon. As a result, the impurities are sublimed out and removed from the melt in the fo
99	TT0029	JP	5635985	The invention describes a process for removing nonmetallic impurities from metallurgical silicon. A melt is produced from metallurgical silicon and halide-containing silicon. As a result, the impurities are sublimed out and removed from the melt in the fo
100	TT0029	JP	5635985	The invention describes a process for removing nonmetallic impurities from metallurgical silicon. A melt is produced from metallurgical silicon and halide-containing silicon. As a result, the impurities are sublimed out and removed from the melt in the fo

101	TT0029	US	13/057,084	The invention describes a process for removing nonmetallic impurities from metallurgical silicon. A melt is produced from metallurgical silicon and halide-containing silicon. As a result, the impurities are sublimed out and removed from the melt in the fo
102	TT0029	US	13/057,084	The invention describes a process for removing nonmetallic impurities from metallurgical silicon. A melt is produced from metallurgical silicon and halide-containing silicon. As a result, the impurities are sublimed out and removed from the melt in the fo
103	TT0031	DE	502009007485.9	The invention relates to a method for producing halogenated oligomers and/or halogenated polymers of elements of the third to fifth main group, wherein the halogenated oligomers and/or halogenated polymers are synthesized from a first chain-forming agent
104	TT0031	FR	2328954	The invention relates to a method for producing halogenated oligomers and/or halogenated polymers of elements of the third to fifth main group, wherein the halogenated oligomers and/or halogenated polymers are synthesized from a first chain-forming agent
105	TT0031	GB	2328954	The invention relates to a method for producing halogenated oligomers and/or halogenated polymers of elements of the third to fifth main group, wherein the halogenated oligomers and/or halogenated polymers are synthesized from a first chain-forming agent
106	TT0031	IN	1158/KOLNP/2011	The invention relates to a method for producing halogenated oligomers and/or halogenated polymers of elements of the third to fifth main group, wherein the halogenated oligomers and/or halogenated polymers are synthesized from a first chain-forming agent
107	TT0031	JP	2011-526370	The invention relates to a method for producing halogenated oligomers and/or halogenated polymers of elements of the third to fifth main group, wherein the halogenated oligomers and/or halogenated polymers are synthesized from a first chain-forming agent
108	TT0033	DE	102009002129.9	The invention relates to bodies, coated by a SiC hard material layer or by a layer system comprising at least one SiC hard material layer, and to a method for producing said type of coated bodies. The aim of the invention is to supply bodies with SiC laye
109	TT0033	EP	2414558	The invention relates to bodies, coated by a SiC hard material layer or by a layer system comprising at least one SiC hard material layer, and to a method for producing said type of coated bodies. The aim of the invention is to supply bodies with SiC laye
110	TT0033	IN	4104/KOLNP/2011	The invention relates to bodies, coated by a SiC hard material layer or by a layer system comprising at least one SiC hard material layer, and to a method for producing said type of coated bodies. The aim of the invention is to supply bodies with SiC laye
111	TT0033	US	9,962,370	The invention relates to bodies, coated by a SiC hard material layer or by a layer system comprising at least one SiC hard material layer, and to a method for producing said type of coated bodies. The aim of the invention is to supply bodies with SiC laye
112	TT0034	IN	1356/KOLNP/2012	The invention relates to a method for removing impurities from silicon, comprising the following steps: A) providing metal silicon comprising impurities, B) mixing the silicon to be purified with at least one halogen polysilane of the formula SiX_n , where
113	TT0034	US	13/513,611	The invention relates to a method for removing impurities from silicon, comprising the following steps: A) providing metal silicon comprising impurities, B) mixing the silicon to be purified with at least one halogen polysilane of the formula SiX_n , where
114	TT0035	CN	ZL201080055163.X	The invention relates to kinetically stable halogenated polysilanes as a mixture of compounds having respectively at least four silicon atoms which are bound together, the substituents thereof comprising chlorine, and chlorine and hydrogen, and in the com
115	TT0035	DE	502010005189.9	The invention relates to kinetically stable halogenated polysilanes as a mixture of compounds having respectively at least four silicon atoms which are bound together, the substituents thereof comprising chlorine, and chlorine and hydrogen, and in the com

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116	TT0035	EP	2507296	The invention relates to kinetically stable halogenated polysilanes as a mixture of compounds having respectively at least four silicon atoms which are bound together, the substituents thereof comprising chlorine, and chlorine and hydrogen, and in the com
117	TT0035	FR	2507296	The invention relates to kinetically stable halogenated polysilanes as a mixture of compounds having respectively at least four silicon atoms which are bound together, the substituents thereof comprising chlorine, and chlorine and hydrogen, and in the com
118	TT0035	GB	2507296	The invention relates to kinetically stable halogenated polysilanes as a mixture of compounds having respectively at least four silicon atoms which are bound together, the substituents thereof comprising chlorine, and chlorine and hydrogen, and in the com
119	TT0035	IN	1322/KOLNP/2012	The invention relates to kinetically stable halogenated polysilanes as a mixture of compounds having respectively at least four silicon atoms which are bound together, the substituents thereof comprising chlorine, and chlorine and hydrogen, and in the com
120	TT0035	JP	5731531	The invention relates to kinetically stable halogenated polysilanes as a mixture of compounds having respectively at least four silicon atoms which are bound together, the substituents thereof comprising chlorine, and chlorine and hydrogen, and in the com
121	TT0035	US	9,040,009	The invention relates to kinetically stable halogenated polysilanes as a mixture of compounds having respectively at least four silicon atoms which are bound together, the substituents thereof comprising chlorine, and chlorine and hydrogen, and in the com
122	TT0036 / TT0038	EP	10787123.8	The invention relates to a method for producing hydrogenated polygermane as a pure compound or as a mixture of compounds, in which halogenated polygermane is hydrogenated. The invention also relates to a hydrogenated polygermane and to a germanium layer p
123	TT0036 / TT0038	IN	1321/KOLNP/2012	The invention relates to a method for producing hydrogenated polygermane as a pure compound or as a mixture of compounds, in which halogenated polygermane is hydrogenated. The invention also relates to a hydrogenated polygermane and to a germanium layer p
124	TT0036 / TT0038	JP	2012-541533	The invention relates to a method for producing hydrogenated polygermane as a pure compound or as a mixture of compounds, in which halogenated polygermane is hydrogenated. The invention also relates to a hydrogenated polygermane and to a germanium layer p
125	TT0037 / TT0039	EP	10788316.7	The invention relates to a method for producing hydrogenated polygermasilane as a pure compound or a mixture of compounds, wherein halogenated polygermasilane is hydrogenated. The invention also relates to a hydrogenated polygermasilane, to a germanium la
126	TT0037 / TT0039	IN	1323/KOLNP/2012	The invention relates to a method for producing hydrogenated polygermasilane as a pure compound or a mixture of compounds, wherein halogenated polygermasilane is hydrogenated. The invention also relates to a hydrogenated polygermasilane, to a germanium la
127	TT0037 / TT0039	JP	2012-541539	The invention relates to a method for producing hydrogenated polygermasilane as a pure compound or a mixture of compounds, wherein halogenated polygermasilane is hydrogenated. The invention also relates to a hydrogenated polygermasilane, to a germanium la
128	TT0040	IN	1355/KOLNP/2012	The invention relates to a method for producing hydrogenated polygermasilane as a pure compound or a mixture of compounds, wherein halogenated polygermasilane is hydrogenated. The invention also relates to a hydrogenated polygermasilane, to a germanium la
129	TT0040	US	13/513,384	The invention relates to a method for producing hydrogenated polygermasilane as a pure compound or a mixture of compounds, wherein halogenated polygermasilane is hydrogenated. The invention also relates to a hydrogenated polygermasilane, to a germanium la

130	TT0042	DE	102009056438	The invention relates to a method for producing hexachlorodisilane. Hexachlorodisilane is obtained by the oxidative splitting of the chlorinated polysilane of the empirical formula SiCl_x ($x = 0,2- 0,8$) using chlorine gas. As a result the hexachlorodisilan
131	TT0042	EP	10785076.0	The invention relates to a method for producing hexachlorodisilane. Hexachlorodisilane is obtained by the oxidative splitting of the chlorinated polysilane of the empirical formula SiCl_x ($x = 0,2- 0,8$) using chlorine gas. As a result the hexachlorodisilan
132	TT0042	IN	1314/KOLNP/2012	The invention relates to a method for producing hexachlorodisilane. Hexachlorodisilane is obtained by the oxidative splitting of the chlorinated polysilane of the empirical formula SiCl_x ($x = 0,2- 0,8$) using chlorine gas. As a result the hexachlorodisilan
133	TT0042	US	13/512,678	The invention relates to a method for producing hexachlorodisilane. Hexachlorodisilane is obtained by the oxidative splitting of the chlorinated polysilane of the empirical formula SiCl_x ($x = 0,2- 0,8$) using chlorine gas. As a result the hexachlorodisilan
134	TT0043	IN	1316/KOLNP/2012	The invention relates to a method and a device for producing short-chained halogenated polysilanes and/or short-chained halogenated polysilanes and halogenide-containing silicon by thermolytic decomposition of long-chained halogenated polysilanes. The the
135	TT0043	US	13/512,905	The invention relates to a method and a device for producing short-chained halogenated polysilanes and/or short-chained halogenated polysilanes and halogenide-containing silicon by thermolytic decomposition of long-chained halogenated polysilanes. The the
136	TT0044	IN	1315/KOLNP/2012	The invention relates to a chlorinated polysilane which has the formula SiCl_x wherein $x = 0,01 - 0,8$ and which can be produced in particular by the thermolysis of a chloropolysilane at a temperature below 600 DEG C.
137	TT0044	JP	5667203	The invention relates to a chlorinated polysilane which has the formula SiCl_x wherein $x = 0,01 - 0,8$ and which can be produced in particular by the thermolysis of a chloropolysilane at a temperature below 600 DEG C.
138	TT0044	US	13/512,461	The invention relates to a chlorinated polysilane which has the formula SiCl_x wherein $x = 0,01 - 0,8$ and which can be produced in particular by the thermolysis of a chloropolysilane at a temperature below 600 DEG C.
139	TT0055	CN	201180035876.4	The invention relates to the generation of hydrogen for operating fuel cells in aircraft, wherein hydrogen is generated by reacting hydrogenated polysilanes (HPS) with water in a reaction chamber. The reaction chamber comprises a feed device and a dischar
140	TT0055	DE	502011005988.4	The invention relates to the generation of hydrogen for operating fuel cells in aircraft, wherein hydrogen is generated by reacting hydrogenated polysilanes (HPS) with water in a reaction chamber. The reaction chamber comprises a feed device and a dischar
141	TT0055	FR	2596541	The invention relates to the generation of hydrogen for operating fuel cells in aircraft, wherein hydrogen is generated by reacting hydrogenated polysilanes (HPS) with water in a reaction chamber. The reaction chamber comprises a feed device and a dischar
142	TT0055	GB	2596541	The invention relates to the generation of hydrogen for operating fuel cells in aircraft, wherein hydrogen is generated by reacting hydrogenated polysilanes (HPS) with water in a reaction chamber. The reaction chamber comprises a feed device and a dischar
143	TT0055	IN	176/KOLNP/2013	The invention relates to the generation of hydrogen for operating fuel cells in aircraft, wherein hydrogen is generated by reacting hydrogenated polysilanes (HPS) with water in a reaction chamber. The reaction chamber comprises a feed device and a

				dischar
144	TT0055	IN	176/KOLNP/2013	The invention relates to the generation of hydrogen for operating fuel cells in aircraft, wherein hydrogen is generated by reacting hydrogenated polysilanes (HPS) with water in a reaction chamber. The reaction chamber comprises a feed device and a dischar
145	TT0055	JP	2013-521072	The invention relates to the generation of hydrogen for operating fuel cells in aircraft, wherein hydrogen is generated by reacting hydrogenated polysilanes (HPS) with water in a reaction chamber. The reaction chamber comprises a feed device and a dischar
146	TT0055	KR	10-2013-7004594	The invention relates to the generation of hydrogen for operating fuel cells in aircraft, wherein hydrogen is generated by reacting hydrogenated polysilanes (HPS) with water in a reaction chamber. The reaction chamber comprises a feed device and a dischar
147	TT0055	KR	10-2013-7004594	The invention relates to the generation of hydrogen for operating fuel cells in aircraft, wherein hydrogen is generated by reacting hydrogenated polysilanes (HPS) with water in a reaction chamber. The reaction chamber comprises a feed device and a dischar
148	TT0055	US	13/811,521	The invention relates to the generation of hydrogen for operating fuel cells in aircraft, wherein hydrogen is generated by reacting hydrogenated polysilanes (HPS) with water in a reaction chamber. The reaction chamber comprises a feed device and a dischar
149	TT0047	CN	ZL201080054817.7	The present invention relates to a method for producing halogenated polysilanes as a pure compound or mixture of compounds, which has a specific purity in relation to inter alia boron-containing compounds. An embodiment of the invention is a method for pr
150	TT0047	DE	502010005346.8	The present invention relates to a method for producing halogenated polysilanes as a pure compound or mixture of compounds, which has a specific purity in relation to inter alia boron-containing compounds. An embodiment of the invention is a method for pr
151	TT0047	EP	2507174	The present invention relates to a method for producing halogenated polysilanes as a pure compound or mixture of compounds, which has a specific purity in relation to inter alia boron-containing compounds. An embodiment of the invention is a method for pr
152	TT0047	FR	2507174	The present invention relates to a method for producing halogenated polysilanes as a pure compound or mixture of compounds, which has a specific purity in relation to inter alia boron-containing compounds. An embodiment of the invention is a method for pr
153	TT0047	GB	2507174	The present invention relates to a method for producing halogenated polysilanes as a pure compound or mixture of compounds, which has a specific purity in relation to inter alia boron-containing compounds. An embodiment of the invention is a method for pr
154	TT0047	IN	1320/KOLNP/2012	The present invention relates to a method for producing halogenated polysilanes as a pure compound or mixture of compounds, which has a specific purity in relation to inter alia boron-containing compounds. An embodiment of the invention is a method for pr
155	TT0047	US	9,139,702	The present invention relates to a method for producing halogenated polysilanes as a pure compound or mixture of compounds, which has a specific purity in relation to inter alia boron-containing compounds. An embodiment of the invention is a method for pr

156	TT0029	DE	102008036143.7	The invention describes a process for removing nonmetallic impurities from metallurgical silicon. A melt is produced from metallurgical silicon and halide containing silicon. As a result, the impurities are submitted out and removed from the melt in the fo
157	TT0040	DE	102009056731.3	The invention relates to a method for producing hydrogenated polygermasilane as a pure compound or a mixture of compounds, wherein halogenated polygermasilane is hydrogenated. The invention also relates to a hydrogenated polygermasilane, to a germanium Ia
158	TT0040	EP	10792879.8	The invention relates to a method for producing hydrogenated polygermasilane as a pure compound or a mixture of compounds, wherein halogenated polygermasilane is hydrogenated. The invention also relates to a hydrogenated polygermasilane, to a germanium Ia
159	TT0041	DE	102009056731.3	The invention relatet to chlorinated oligogermanes as a pure compund or as a mixture of compounds, and to a method for the production thereof. The chlorinated oligogermanes as a pure compound or a mixture of compounds respectively comprise at least one d
160	TT0041	EP	10787451.3	The invention relatet to chlorinated oligogermanes as a pure compound or as a mixture of compounds, and to a method for the production thereof. The chlorinated oligogermanes as a pure compound or a mixture of compounds respectively comprise at least one d
161	TT0043	DE	102009056437.3	The invention relates to a method and a device for producing short chained halogenated polysilanes and/or short chaind halogenated polysilanes and halogenide containing silicon by thermolytic decomposition of long chained halogenated polysilanes. The the
162	TT0043	EP	10787414.1	The invention relates to a method and a device for producing short chained halogenated polysilanes and/or short chaind halogenated polysilanes and halogenide containing silicon by thermolytic decomposition of long chained halogenated polysilanes. The the
163	TT0048	DE	102010025710.9	The invention relatet to a storage material for obtaining H-silanes which is present in the form of a hydrogenated polysilane (HPS), as a pure compound or as a mixture of compounds having on average at least six direct Si-Si bonds, the substituents of whi.
164	TT0048	EP	11757745.2	The invention relatet to a storage material for obtaining H-silanes which is present in the form of a hydrogenated polysilane (HPS), as a pure compound or as a mixture of compounds having on average at least six direct Si-Si bonds, the substituents of whi.
165	TT0049	DE	102010025948.9	The invention relates to polysilanes of medium chain length as pure compounds or a mixture of compounds, each with at least one direct Si-Si bond, the substituents of said polysilanes consisting exclusively of halogen and/or hydrogen, the medium chain len
166	TT0049	EP	11730630.8	The invention relates to polysilanes of medium chain length as pure compounds or a mixture of compounds, each with at least one direct Si-Si bond, the substituents of said polysilanes consisting exclusively of halogen and/or hydrogen, the medium chain len
167	TT0053	DE	102010019874.9	The invention relates to nano-wires which consists of or comprise semiconductor materilas and are used for applications in photovoltaics and electronics and to a method for the production thereof. The nano wires are characerized in that they are obtained
168	TT0053	EP	11720073.3	The invention relates to nano-wires which consists of or comprise semiconductor materilas and are used for applications in photovoltaics and electronics and to a method for the production thereof. The nano wires are characerized in that they are obtained
169	TT0056	DE	102012108250.2	One embodiment of the invention concerns a method for depositing Si layers or substrates, there being deposited on a substrate in a chemical gas phase process layers of silicon from at least one precursor which is selected from halogenosilane

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170	TT0056	EP	13753307.1	One embodiment of the invention concerns a method for depositing Si layers or substrates, there being deposited on a substrate in a chemical gas phase process layers of silicon from at least one precursor which is selected from halogenosilane compounds of
171	TT0056	WO	PCT/EP2013/067150	One embodiment of the invention concerns a method for depositing Si layers or substrates, there being deposited on a substrate in a chemical gas phase process layers of silicon from at least one precursor which is selected from halogenosilane compounds of
172	TT0067	DE	To Be Filed	Base catalyzed formation of higher halogenated oligosilanes from hexahalogenosilanes.

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Annex 2
Power of attorney

Nagarjuna Industrial Services and Investments Private Ltd.(Nagarjuna Mauritius), registered in the commercial register of Mauritius under register number 094708, Suite G12, St. James Court, St. Denis Street, Port Louis, Mauritius

hereby grants power of attorney to

Nagarjuna Fertilizers and Chemicals Limited (NFCL), a Public Company Limited by Shares, registered under the Companies Act, 1956 with Corporate Identification number (CIN) L24129AP2006PLC076238, having its registered office at D.No.8-2-248, Nagarjuna Hills, Punjagutta, Hyderabad, Telangana – 500 082("NFCL.");

entitling NFCL. to

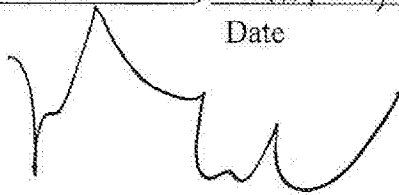
make any declaration on behalf of **Nagarjuna Mauritius**. necessary to transfer or to enforce, exercise, complete, or register a transfer of any intellectual property right of **Nagarjuna Mauritius.**, particularly including but not limited to patents and patent applications listed in the Annex hereto, to NFCL (the "Power of Attorney").

This Power of Attorney particularly includes the right of NFCL. to make declarations on behalf of **Nagarjuna Mauritius** vis-a-vis any authority, in particular vis-a-vis any patent and trademark office worldwide. This particularly includes any declaration made in order to arrange for the registration (i) of a transfer of intellectual property rights from **Nagarjuna Mauritius** to NFCL and/or (ii) of NFCL as the new owner of intellectual property rights for which **Nagarjuna Mauritius** is currently the registered owner.

NFCL is released from any potential restrictions, if any, such as restrictions in regard of self-dealing.

This power of attorney is governed by the laws of India.

Mauritius, MAY 12, 2016
Place Date



for and on behalf of Nagarjuna Industrial Services and Investments Private Limited.

Annex

to the Power of Attorney granted by Nagarjuna Industrial Services and Investments Private
Limited to Nagarjuna Fertilizers and Chemicals Limited

S. No	Reference	Country	Application / Publication / Patent Number	Abstract
1	TT0004	AT	E410396	The present invention relates to a method for the production of silicon from silyl halides. In a first step, the silyl halide is converted, with the generation of a plasma discharge, to a halogenated polysilane, which is subsequently decomposed to silicon
2	TT0004	CN	ZL200680017874.1	The present invention relates to a method for the production of silicon from silyl halides. In a first step, the silyl halide is converted, with the generation of a plasma discharge, to a halogenated polysilane, which is subsequently decomposed to silicon
3	TT0004	DE	102005024041.00	The present invention relates to a method for the production of silicon from silyl halides. In a first step, the silyl halide is converted, with the generation of a plasma discharge, to a halogenated polysilane, which is subsequently decomposed to silicon
4	TT0004	DE	502006001783.0	The present invention relates to a method for the production of silicon from silyl halides. In a first step, the silyl halide is converted, with the generation of a plasma discharge, to a halogenated polysilane, which is subsequently decomposed to silicon
5	TT0004	FR	1896362	The present invention relates to a method for the production of silicon from silyl halides. In a first step, the silyl halide is converted, with the generation of a plasma discharge, to a halogenated polysilane, which is subsequently decomposed to silicon
6	TT0004	GB	1896362	The present invention relates to a method for the production of silicon from silyl halides. In a first step, the silyl halide is converted, with the generation of a plasma discharge, to a halogenated polysilane, which is subsequently decomposed to silicon
7	TT0004	IT	19070BE/2009	The present invention relates to a method for the production of silicon from silyl halides. In a first step, the silyl halide is converted, with the generation of a plasma discharge, to a halogenated polysilane, which is subsequently decomposed to silicon
8	TT0004	JP	4832511	The present invention relates to a method for the production of silicon from silyl halides. In a first step, the silyl halide is converted, with the generation of a plasma discharge, to a halogenated polysilane, which is subsequently decomposed to silicon
9	TT0004	US	8,147,656	The present invention relates to a method for the production of silicon from silyl halides. In a first step, the silyl halide is converted, with the generation of a plasma discharge, to a halogenated polysilane, which is subsequently decomposed to silicon
11	TT0005	DE	102005053781	Hydrogen generation for operating fuel cells, comprises reacting silicon and/or a silicon-containing alloy with an alkaline solution as catalyst, in a reaction vessel (1) to form silicon dioxide as nucleator, and depositing the formed silicon dioxide on c
12	TT0005	DE	102006020786	Hydrogen generation for operating fuel cells, comprises reacting silicon and/or a silicon-containing alloy with an alkaline solution as catalyst, in a reaction vessel (1) to form silicon dioxide as nucleator, and depositing the formed silicon dioxide on c
13	TT0005	EP	6818429.00	Hydrogen generation for operating fuel cells, comprises reacting silicon and/or a silicon-containing alloy with an alkaline solution as catalyst, in a reaction vessel (1) to form silicon dioxide as

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				nucleator, and depositing the formed silicon dioxide on c
14	TT0006	AU	2007276384	The invention relates to a method for the final product-related manufacture of low-molecular, medium-molecular, and high-molecular halogenated polysilanes, the distillation thereof into selected fractions, the direct deposition of silicon from the gas pha
15	TT0008	AU	2013224703.00	The invention relates to a method for the final product-related manufacture of low-molecular, medium-molecular, and high-molecular halogenated polysilanes, the distillation thereof into selected fractions, the direct deposition of silicon from the gas pha
16	TT0006	CN	ZL200780030815.2	The invention relates to a method for the final product-related manufacture of low-molecular, medium-molecular, and high-molecular halogenated polysilanes, the distillation thereof into selected fractions, the direct deposition of silicon from the gas pha
17	TT0008	DE	102006034061.20	The invention relates to a method for the final product-related manufacture of low-molecular, medium-molecular, and high-molecular halogenated polysilanes, the distillation thereof into selected fractions, the direct deposition of silicon from the gas pha
18	TT0006	EP	11167143.40	The invention relates to a method for the final product-related manufacture of low-molecular, medium-molecular, and high-molecular halogenated polysilanes, the distillation thereof into selected fractions, the direct deposition of silicon from the gas pha
19	TT0006	EP	2361945	The invention relates to a method for the final product-related manufacture of low-molecular, medium-molecular, and high-molecular halogenated polysilanes, the distillation thereof into selected fractions, the direct deposition of silicon from the gas pha
20	TT0006	EP	2361946	The invention relates to a method for the final product-related manufacture of low-molecular, medium-molecular, and high-molecular halogenated polysilanes, the distillation thereof into selected fractions, the direct deposition of silicon from the gas pha
21	TT0006	EP	2361943	The invention relates to a method for the final product-related manufacture of low-molecular, medium-molecular, and high-molecular halogenated polysilanes, the distillation thereof into selected fractions, the direct deposition of silicon from the gas pha
22	TT0006	EP	2044143	The invention relates to a method for the final product-related manufacture of low-molecular, medium-molecular, and high-molecular halogenated polysilanes, the distillation thereof into selected fractions, the direct deposition of silicon from the gas pha
23	TT0006	JP	5520602	The invention relates to a method for the final product-related manufacture of low-molecular, medium-molecular, and high-molecular halogenated polysilanes, the distillation thereof into selected fractions, the direct deposition of silicon from the gas pha
24	TT0007	AT	E508.983	The invention relates to a process for preparing hydrogen. According to the invention, monosilane or polysilane is converted to hydrogen at an elevated temperature with steam or oxygen.
25	TT0007	CN	101573288.00	The invention relates to a process for preparing hydrogen. According to the invention, monosilane or polysilane is converted to hydrogen at an elevated temperature with steam or oxygen.
26	TT0007	DE	502007007189.7	The invention relates to a process for preparing hydrogen. According to the invention, monosilane or polysilane is converted to hydrogen at an elevated temperature with steam or oxygen.

27	TT0007	ES	2043949	The invention relates to a process for preparing hydrogen. According to the invention, monosilane or polysilane is converted to hydrogen at an elevated temperature with steam or oxygen.
28	TT0007	FR	2043949	The invention relates to a process for preparing hydrogen. According to the invention, monosilane or polysilane is converted to hydrogen at an elevated temperature with steam or oxygen.
29	TT0007	GB	2043949	The invention relates to a process for preparing hydrogen. According to the invention, monosilane or polysilane is converted to hydrogen at an elevated temperature with steam or oxygen.
30	TT0007	IN	239/KOLNP/2009	The invention relates to a process for preparing hydrogen. According to the invention, monosilane or polysilane is converted to hydrogen at an elevated temperature with steam or oxygen.
31	TT0007	IT	2043949	The invention relates to a process for preparing hydrogen. According to the invention, monosilane or polysilane is converted to hydrogen at an elevated temperature with steam or oxygen.
32	TT0007	JP	5249216	The invention relates to a process for preparing hydrogen. According to the invention, monosilane or polysilane is converted to hydrogen at an elevated temperature with steam or oxygen.
33	TT0007	US	8,414,863	The invention relates to a process for preparing hydrogen. According to the invention, monosilane or polysilane is converted to hydrogen at an elevated temperature with steam or oxygen.
34	TT0008	CN	ZL200780029023.3	Process for supplying a fuel cell with hydrogen, which includes the steps:-intermediate storage of (poly)silanes or (poly)silane solutions-transfer of the (poly)silanes to a reaction chamber-reaction or hydrolysis of the silanes or silane solutions in the
35	TT0008	EP	2047552.00	Process for supplying a fuel cell with hydrogen, which includes the steps:-intermediate storage of (poly)silanes or (poly)silane solutions-transfer of the (poly)silanes to a reaction chamber-reaction or hydrolysis of the silanes or silane solutions in the
36	TT0008	IN	434/KOLNP/2009	Process for supplying a fuel cell with hydrogen, which includes the steps:-intermediate storage of (poly)silanes or (poly)silane solutions-transfer of the (poly)silanes to a reaction chamber-reaction or hydrolysis of the silanes or silane solutions in the
37	TT0008	JP	5448815	Process for supplying a fuel cell with hydrogen, which includes the steps:-intermediate storage of (poly)silanes or (poly)silane solutions-transfer of the (poly)silanes to a reaction chamber-reaction or hydrolysis of the silanes or silane solutions in the
38	TT0008	US	8,435,476	Process for supplying a fuel cell with hydrogen, which includes the steps:-intermediate storage of (poly)silanes or (poly)silane solutions-transfer of the (poly)silanes to a reaction chamber-reaction or hydrolysis of the silanes or silane solutions in the
39	TT0008	US	13/848,573	Process for supplying a fuel cell with hydrogen, which includes the steps:-intermediate storage of (poly)silanes or (poly)silane solutions-transfer of the (poly)silanes to a reaction chamber-reaction or hydrolysis of the silanes or silane solutions in the
40	TT0009	DE	102006043929	The invention is directed to mixtures of polysilanes macroscopically solid at ambient temperature wherein the individual components of the composition Si_nH_{2n} and/or $\text{Si}_n\text{H}_{2n+2}$ of which decompose before they are boiling at an applied process pressure and whi
41	TT0009	EP	2064267	The invention is directed to mixtures of polysilanes macroscopically solid at ambient temperature wherein the individual components of the composition Si_nH_{2n} and/or $\text{Si}_n\text{H}_{2n+2}$ of which decompose before they are boiling at an applied process pressure and whi
42	TT0009	US	8,177,943	The invention is directed to mixtures of polysilanes macroscopically solid at ambient temperature wherein the individual components of the composition Si_nH_{2n} and/or $\text{Si}_n\text{H}_{2n+2}$ of which decompose before they are boiling at an applied process pressure and whi
43	TT0013	DE	102007013219	The invention is based on the aim of developing a device and a method for the plasma-enhanced synthesis of halogenated polysilanes and polygermanes, wherein at least one reaction

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				partner is present in a gaseous form and is excited by reactive particles fr
44	TT0013	EP	2137236	The invention is based on the aim of developing a device and a method for the plasma-enhanced synthesis of halogenated polysilanes and polygermanes, wherein at least one reaction partner is present in a gaseous form and is excited by reactive particles fr
45	TT0013	IN	1931/MUMNP/2009	The invention is based on the aim of developing a device and a method for the plasma-enhanced synthesis of halogenated polysilanes and polygermanes, wherein at least one reaction partner is present in a gaseous form and is excited by reactive particles fr
46	TT0013	JP	5415290	The invention is based on the aim of developing a device and a method for the plasma-enhanced synthesis of halogenated polysilanes and polygermanes, wherein at least one reaction partner is present in a gaseous form and is excited by reactive particles fr
47	TT0013	KR	10-2009-7021530	The invention is based on the aim of developing a device and a method for the plasma-enhanced synthesis of halogenated polysilanes and polygermanes, wherein at least one reaction partner is present in a gaseous form and is excited by reactive particles fr
48	TT0013	US	12/530,662	The invention is based on the aim of developing a device and a method for the plasma-enhanced synthesis of halogenated polysilanes and polygermanes, wherein at least one reaction partner is present in a gaseous form and is excited by reactive particles fr
49	TT0014	AT	E508.985	The invention relates to a method for the catalytic hydrogenation of halogenated silanes or halogenated germanes, according to which halogenated monosilanes, oligosilanes or polysilanes, or monogermanes, oligogermanes or polygermanes, are hydrogenated or
50	TT0014	CN	ZL200880018321.7	The invention relates to a method for the catalytic hydrogenation of halogenated silanes or halogenated germanes, according to which halogenated monosilanes, oligosilanes or polysilanes, or monogermanes, oligogermanes or polygermanes, are hydrogenated or
51	TT0014	DE	502008003497.8	The invention relates to a method for the catalytic hydrogenation of halogenated silanes or halogenated germanes, according to which halogenated monosilanes, oligosilanes or polysilanes, or monogermanes, oligogermanes or polygermanes, are hydrogenated or
52	TT0014	ES	2366597	The invention relates to a method for the catalytic hydrogenation of halogenated silanes or halogenated germanes, according to which halogenated monosilanes, oligosilanes or polysilanes, or monogermanes, oligogermanes or polygermanes, are hydrogenated or
53	TT0014	FR	2132137	The invention relates to a method for the catalytic hydrogenation of halogenated silanes or halogenated germanes, according to which halogenated monosilanes, oligosilanes or polysilanes, or monogermanes, oligogermanes or polygermanes, are hydrogenated or
54	TT0014	GB	2132137	The invention relates to a method for the catalytic hydrogenation of halogenated silanes or halogenated germanes, according to which halogenated monosilanes, oligosilanes or polysilanes, or monogermanes, oligogermanes or polygermanes, are hydrogenated or
55	TT0014	IN	264800	The invention relates to a method for the catalytic hydrogenation of halogenated silanes or halogenated germanes, according to which halogenated monosilanes, oligosilanes or polysilanes, or monogermanes, oligogermanes or polygermanes, are hydrogenated or

56	TT0014	IT	2132137	The invention relates to a method for the catalytic hydrogenation of halogenated silanes or halogenated germanes, according to which halogenated monosilanes, oligosilanes or polysilanes, or monogermanes, oligogermanes or polygermanes, are hydrogenated or
57	TT0014	KR	10-2009-7022832	The invention relates to a method for the catalytic hydrogenation of halogenated silanes or halogenated germanes, according to which halogenated monosilanes, oligosilanes or polysilanes, or monogermanes, oligogermanes or polygermanes, are hydrogenated or
58	TT0014	US	8,372,370	The invention relates to a method for the catalytic hydrogenation of halogenated silanes or halogenated germanes, according to which halogenated monosilanes, oligosilanes or polysilanes, or monogermanes, oligogermanes or polygermanes, are hydrogenated or
59	TT0015	CN	ZL200880018219.7	The invention relates to a method for the plasma-assisted synthesis of organohalosilanes in which organohalosilanes of the general empirical formula $R_1mR_2oS_iX_4-p$ ($X=F, Cl, Br$ or I ; $p=1-4$; $p=m+o$; $m=1-4$; $o=0-3$; $R_1, R_2 =$ alkyl, alkenyl, alkynyl, aryl) and/
60	TT0015	DE	502008008109.7	The invention relates to a method for the plasma-assisted synthesis of organohalosilanes in which organohalosilanes of the general empirical formula $R_1mR_2oS_iX_4-p$ ($X=F, Cl, Br$ or I ; $p=1-4$; $p=m+o$; $m=1-4$; $o=0-3$; $R_1, R_2 =$ alkyl, alkenyl, alkynyl, aryl) and/
61	TT0015	ES	2142557	The invention relates to a method for the plasma-assisted synthesis of organohalosilanes in which organohalosilanes of the general empirical formula $R_1mR_2oS_iX_4-p$ ($X=F, Cl, Br$ or I ; $p=1-4$; $p=m+o$; $m=1-4$; $o=0-3$; $R_1, R_2 =$ alkyl, alkenyl, alkynyl, aryl) and/
62	TT0015	FR	2142557	The invention relates to a method for the plasma-assisted synthesis of organohalosilanes in which organohalosilanes of the general empirical formula $R_1mR_2oS_iX_4-p$ ($X=F, Cl, Br$ or I ; $p=1-4$; $p=m+o$; $m=1-4$; $o=0-3$; $R_1, R_2 =$ alkyl, alkenyl, alkynyl, aryl) and/
63	TT0015	GB	2142557	The invention relates to a method for the plasma-assisted synthesis of organohalosilanes in which organohalosilanes of the general empirical formula $R_1mR_2oS_iX_4-p$ ($X=F, Cl, Br$ or I ; $p=1-4$; $p=m+o$; $m=1-4$; $o=0-3$; $R_1, R_2 =$ alkyl, alkenyl, alkynyl, aryl) and/
64	TT0015	IN	2032/MUMNP/2009	The invention relates to a method for the plasma-assisted synthesis of organohalosilanes in which organohalosilanes of the general empirical formula $R_1mR_2oS_iX_4-p$ ($X=F, Cl, Br$ or I ; $p=1-4$; $p=m+o$; $m=1-4$; $o=0-3$; $R_1, R_2 =$ alkyl, alkenyl, alkynyl, aryl) and/
65	TT0015	IT	2142557	The invention relates to a method for the plasma-assisted synthesis of organohalosilanes in which organohalosilanes of the general empirical formula $R_1mR_2oS_iX_4-p$ ($X=F, Cl, Br$ or I ; $p=1-4$; $p=m+o$; $m=1-4$; $o=0-3$; $R_1, R_2 =$ alkyl, alkenyl, alkynyl, aryl) and/
66	TT0015	US	2011-0132744	The invention relates to a method for the plasma-assisted synthesis of organohalosilanes in which organohalosilanes of the general empirical formula $R_1mR_2oS_iX_4-p$ ($X=F, Cl, Br$ or I ; $p=1-4$; $p=m+o$; $m=1-4$; $o=0-3$; $R_1, R_2 =$ alkyl, alkenyl, alkynyl, aryl) and/
67	TT0020	AU	2009253523	The invention relates to a halogenated polysilane (referred to in the following as polysilane) as a pure compound or as a mixture of compounds and to a thermal process for producing the same. The polysilane is characterized by characteristic shifts in its
68	TT0020	CA	2,725,366	The invention relates to a halogenated polysilane (referred to in the following as polysilane) as a pure compound or as a mixture of compounds and to a thermal process for producing the same. The polysilane is characterized by characteristic shifts in its
69	TT0020	CN	ZL200980119335.2	The invention relates to a halogenated polysilane (referred to in the following as polysilane) as a pure compound or as a mixture of compounds and to a thermal process for producing the same.

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				The polysilane is characterized by characteristic shifts in its
70	TT0020	DE	102008025260	The invention relates to a halogenated polysilane (referred to in the following as polysilane) as a pure compound or as a mixture of compounds and to a thermal process for producing the same. The polysilane is characterized by characteristic shifts in its
71	TT0020	DE	502009008986.4	The invention relates to a halogenated polysilane (referred to in the following as polysilane) as a pure compound or as a mixture of compounds and to a thermal process for producing the same. The polysilane is characterized by characteristic shifts in its
72	TT0020	EP	2296804	The invention relates to a halogenated polysilane (referred to in the following as polysilane) as a pure compound or as a mixture of compounds and to a thermal process for producing the same. The polysilane is characterized by characteristic shifts in its
73	TT0020	FR	2296804	The invention relates to a halogenated polysilane (referred to in the following as polysilane) as a pure compound or as a mixture of compounds and to a thermal process for producing the same. The polysilane is characterized by characteristic shifts in its
74	TT0020	GB	2296804	The invention relates to a halogenated polysilane (referred to in the following as polysilane) as a pure compound or as a mixture of compounds and to a thermal process for producing the same. The polysilane is characterized by characteristic shifts in its
75	TT0020	IN	4489/KOLNP/2010	The invention relates to a halogenated polysilane (referred to in the following as polysilane) as a pure compound or as a mixture of compounds and to a thermal process for producing the same. The polysilane is characterized by characteristic shifts in its
76	TT0020	JP	5639047	The invention relates to a halogenated polysilane (referred to in the following as polysilane) as a pure compound or as a mixture of compounds and to a thermal process for producing the same. The polysilane is characterized by characteristic shifts in its
77	TT0020	KR	10-2010-7029330	The invention relates to a halogenated polysilane (referred to in the following as polysilane) as a pure compound or as a mixture of compounds and to a thermal process for producing the same. The polysilane is characterized by characteristic shifts in its
78	TT0020	US	12/995,174	The invention relates to a halogenated polysilane (referred to in the following as polysilane) as a pure compound or as a mixture of compounds and to a thermal process for producing the same. The polysilane is characterized by characteristic shifts in its
79	TT0021	AU	2009253522	The invention relates to a halogenated polysilane (referred to in the following as polysilane) as a pure compound or as a mixture of compounds and to a plasma-chemical process for producing the same. The polysilane is particularly soluble and fusible and
80	TT0021	CA	2,726,000	The invention relates to a halogenated polysilane (referred to in the following as polysilane) as a pure compound or as a mixture of compounds and to a plasma-chemical process for producing the same. The polysilane is particularly soluble and fusible and
81	TT0021	DE	502009007550.2	The invention relates to a halogenated polysilane (referred to in the following as polysilane) as a pure compound or as a mixture of compounds and to a plasma-chemical process for producing the same. The polysilane is particularly soluble and fusible and
82	TT0021	DE	102008025261	The invention relates to a halogenated polysilane (referred to in the following as polysilane) as a pure compound or as a mixture of compounds and to a plasma-chemical process for producing the same. The polysilane is particularly soluble and fusible and
83	TT0021	EP	2296803	The invention relates to a halogenated polysilane (referred to in the following as polysilane) as a pure compound or as a mixture of compounds and to a plasma-chemical process for producing the same. The polysilane is particularly soluble and fusible and
84	TT0021	FR	2296803	The invention relates to a halogenated polysilane (referred to in the following as polysilane) as a pure compound or as a mixture of compounds and to a plasma-chemical process for producing the same. The polysilane is particularly soluble and fusible and

85	TT0021	GB	2296803	The invention relates to a halogenated polysilane (referred to in the following as polysilane) as a pure compound or as a mixture of compounds and to a plasma-chemical process for producing the same. The polysilane is particularly soluble and fusible and
86	TT0021	IN	4503/KOLNP/2010	The invention relates to a halogenated polysilane (referred to in the following as polysilane) as a pure compound or as a mixture of compounds and to a plasma-chemical process for producing the same. The polysilane is particularly soluble and fusible and
87	TT0021	JP	5658143	The invention relates to a halogenated polysilane (referred to in the following as polysilane) as a pure compound or as a mixture of compounds and to a plasma-chemical process for producing the same. The polysilane is particularly soluble and fusible and
88	TT0021	KR	10-2010-7029329	The invention relates to a halogenated polysilane (referred to in the following as polysilane) as a pure compound or as a mixture of compounds and to a plasma-chemical process for producing the same. The polysilane is particularly soluble and fusible and
89	TT0021	US	12/995,173	The invention relates to a halogenated polysilane (referred to in the following as polysilane) as a pure compound or as a mixture of compounds and to a plasma-chemical process for producing the same. The polysilane is particularly soluble and fusible and
90	TT0022/0023	DE	502009010066.3	The invention relates to silicon containing halogenide obtained by thermal disintegration of halogenized polysilane, and a method for producing the silicon. The silicon has a halogenide content of 1 at%-50 at%. The invention further relates to the use of
91	TT0022/0023	DE	102008025263	The invention relates to silicon containing halogenide obtained by thermal disintegration of halogenized polysilane, and a method for producing the silicon. The silicon has a halogenide content of 1 at%-50 at%. The invention further relates to the use of
92	TT0022/0023	FR	2300368	The invention relates to silicon containing halogenide obtained by thermal disintegration of halogenized polysilane, and a method for producing the silicon. The silicon has a halogenide content of 1 at%-50 at%. The invention further relates to the use of
93	TT0022/0023	GB	2300368	The invention relates to silicon containing halogenide obtained by thermal disintegration of halogenized polysilane, and a method for producing the silicon. The silicon has a halogenide content of 1 at%-50 at%. The invention further relates to the use of
94	TT0022/0023	IN	4989/KOLNP/2010	The invention relates to silicon containing halogenide obtained by thermal disintegration of halogenized polysilane, and a method for producing the silicon. The silicon has a halogenide content of 1 at%-50 at%. The invention further relates to the use of
95	TT0022/0023	KR	10-2010-7029324	The invention relates to silicon containing halogenide obtained by thermal disintegration of halogenized polysilane, and a method for producing the silicon. The silicon has a halogenide content of 1 at%-50 at%. The invention further relates to the use of
96	TT0029	EP	09771469.5	The invention describes a process for removing nonmetallic impurities from metallurgical silicon. A melt is produced from metallurgical silicon and halide-containing silicon. As a result, the impurities are sublimed out and removed from the melt in the fo
97	TT0029	EP	09771469.5	The invention describes a process for removing nonmetallic impurities from metallurgical silicon. A melt is produced from metallurgical silicon and halide-containing silicon. As a result, the impurities are sublimed out and removed from the melt in the fo
98	TT0029	IN	565/KOLNP/2011	The invention describes a process for removing nonmetallic impurities from metallurgical silicon. A melt is produced from metallurgical silicon and halide-containing silicon. As a result, the impurities are sublimed out and removed from the melt in the fo
99	TT0029	JP	5635985	The invention describes a process for removing nonmetallic impurities from metallurgical silicon. A melt is produced from metallurgical silicon and halide-containing silicon. As a result, the impurities are sublimed out and removed from the melt in the fo
100	TT0029	JP	5635985	The invention describes a process for removing nonmetallic impurities from metallurgical silicon. A melt is produced from metallurgical silicon and halide-containing silicon. As a result, the impurities are sublimed out and removed from the melt in the fo

101	TT0029	US	13/057,084	The invention describes a process for removing nonmetallic impurities from metallurgical silicon. A melt is produced from metallurgical silicon and halide-containing silicon. As a result, the impurities are sublimed out and removed from the melt in the fo
102	TT0029	US	13/057,084	The invention describes a process for removing nonmetallic impurities from metallurgical silicon. A melt is produced from metallurgical silicon and halide-containing silicon. As a result, the impurities are sublimed out and removed from the melt in the fo
103	TT0031	DE	502009007485.9	The invention relates to a method for producing halogenated oligomers and/or halogenated polymers of elements of the third to fifth main group, wherein the halogenated oligomers and/or halogenated polymers are synthesized from a first chain-forming agent
104	TT0031	FR	2328954	The invention relates to a method for producing halogenated oligomers and/or halogenated polymers of elements of the third to fifth main group, wherein the halogenated oligomers and/or halogenated polymers are synthesized from a first chain-forming agent
105	TT0031	GB	2328954	The invention relates to a method for producing halogenated oligomers and/or halogenated polymers of elements of the third to fifth main group, wherein the halogenated oligomers and/or halogenated polymers are synthesized from a first chain-forming agent
106	TT0031	IN	1158/KOLNP/2011	The invention relates to a method for producing halogenated oligomers and/or halogenated polymers of elements of the third to fifth main group, wherein the halogenated oligomers and/or halogenated polymers are synthesized from a first chain-forming agent
107	TT0031	JP	2011-526370	The invention relates to a method for producing halogenated oligomers and/or halogenated polymers of elements of the third to fifth main group, wherein the halogenated oligomers and/or halogenated polymers are synthesized from a first chain-forming agent
108	TT0033	DE	102009002129.9	The invention relates to bodies, coated by a SiC hard material layer or by a layer system comprising at least one SiC hard material layer, and to a method for producing said type of coated bodies. The aim of the invention is to supply bodies with SiC laye
109	TT0033	EP	2414558	The invention relates to bodies, coated by a SiC hard material layer or by a layer system comprising at least one SiC hard material layer, and to a method for producing said type of coated bodies. The aim of the invention is to supply bodies with SiC laye
110	TT0033	IN	4104/KOLNP/2011	The invention relates to bodies, coated by a SiC hard material layer or by a layer system comprising at least one SiC hard material layer, and to a method for producing said type of coated bodies. The aim of the invention is to supply bodies with SiC laye
111	TT0033	US	9,062,370	The invention relates to bodies, coated by a SiC hard material layer or by a layer system comprising at least one SiC hard material layer, and to a method for producing said type of coated bodies. The aim of the invention is to supply bodies with SiC laye
112	TT0034	IN	1356/KOLNP/2012	The invention relates to a method for removing impurities from silicon, comprising the following steps: A) providing metal silicon comprising impurities, B) mixing the silicon to be purified with at least one halogen polysilane of the formula SiX_n , where
113	TT0034	US	13/513,611	The invention relates to a method for removing impurities from silicon, comprising the following steps: A) providing metal silicon comprising impurities, B) mixing the silicon to be purified with at least one halogen polysilane of the formula SiX_n , where
114	TT0035	CN	ZL201080055163.X	The invention relates to kinetically stable halogenated polysilanes as a mixture of compounds having respectively at least four silicon atoms which are bound together, the substituents thereof comprising chlorine, and chlorine and hydrogen, and in the com
115	TT0035	DE	502010005189.9	The invention relates to kinetically stable halogenated polysilanes as a mixture of compounds having respectively at least four silicon atoms which are bound together, the substituents thereof comprising chlorine, and chlorine and hydrogen, and in the com

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116	TT0035	EP	2507296	The invention relates to kinetically stable halogenated polysilanes as a mixture of compounds having respectively at least four silicon atoms which are bound together, the substituents thereof comprising chlorine, and chlorine and hydrogen, and in the com
117	TT0035	FR	2507296	The invention relates to kinetically stable halogenated polysilanes as a mixture of compounds having respectively at least four silicon atoms which are bound together, the substituents thereof comprising chlorine, and chlorine and hydrogen, and in the com
118	TT0035	GB	2507296	The invention relates to kinetically stable halogenated polysilanes as a mixture of compounds having respectively at least four silicon atoms which are bound together, the substituents thereof comprising chlorine, and chlorine and hydrogen, and in the com
119	TT0035	IN	1322/KOLNP/2012	The invention relates to kinetically stable halogenated polysilanes as a mixture of compounds having respectively at least four silicon atoms which are bound together, the substituents thereof comprising chlorine, and chlorine and hydrogen, and in the com
120	TT0035	JP	5731531	The invention relates to kinetically stable halogenated polysilanes as a mixture of compounds having respectively at least four silicon atoms which are bound together, the substituents thereof comprising chlorine, and chlorine and hydrogen, and in the com
121	TT0035	US	9,040,009	The invention relates to kinetically stable halogenated polysilanes as a mixture of compounds having respectively at least four silicon atoms which are bound together, the substituents thereof comprising chlorine, and chlorine and hydrogen, and in the com
122	TT0036 / TT0038	EP	10787123.8	The invention relates to a method for producing hydrogenated polygermane as a pure compound or as a mixture of compounds, in which halogenated polygermane is hydrogenated. The invention also relates to a hydrogenated polygermane and to a germanium layer p
123	TT0036 / TT0038	IN	1321/KOLNP/2012	The invention relates to a method for producing hydrogenated polygermane as a pure compound or as a mixture of compounds, in which halogenated polygermane is hydrogenated. The invention also relates to a hydrogenated polygermane and to a germanium layer p
124	TT0036 / TT0038	JP	2012-541533	The invention relates to a method for producing hydrogenated polygermane as a pure compound or as a mixture of compounds, in which halogenated polygermane is hydrogenated. The invention also relates to a hydrogenated polygermane and to a germanium layer p
125	TT0037 / TT0039	EP	10788316.7	The invention relates to a method for producing hydrogenated polygermasilane as a pure compound or a mixture of compounds, wherein halogenated polygermasilane is hydrogenated. The invention also relates to a hydrogenated polygermasilane, to a germanium la
126	TT0037 / TT0039	IN	1323/KOLNP/2012	The invention relates to a method for producing hydrogenated polygermasilane as a pure compound or a mixture of compounds, wherein halogenated polygermasilane is hydrogenated. The invention also relates to a hydrogenated polygermasilane, to a germanium la
127	TT0037 / TT0039	JP	2012-541539	The invention relates to a method for producing hydrogenated polygermasilane as a pure compound or a mixture of compounds, wherein halogenated polygermasilane is hydrogenated. The invention also relates to a hydrogenated polygermasilane, to a germanium la
128	TT0040	IN	1355/KOLNP/2012	The invention relates to a method for producing hydrogenated polygermasilane as a pure compound or a mixture of compounds, wherein halogenated polygermasilane is hydrogenated. The invention also relates to a hydrogenated polygermasilane, to a germanium la
129	TT0040	US	13/513,384	The invention relates to a method for producing hydrogenated polygermasilane as a pure compound or a mixture of compounds, wherein halogenated polygermasilane is hydrogenated. The invention also relates to a hydrogenated polygermasilane, to a germanium la

130	TT0042	DE	102009056438	The invention relates to a method for producing hexachlorodisilane. Hexachlorodisilane is obtained by the oxidative splitting of the chlorinated polysilane of the empirical formula SiCl_x ($x = 0,2- 0,8$) using chlorine gas. As a result the hexachlorodisilan
131	TT0042	EP	10785076.0	The invention relates to a method for producing hexachlorodisilane. Hexachlorodisilane is obtained by the oxidative splitting of the chlorinated polysilane of the empirical formula SiCl_x ($x = 0,2- 0,8$) using chlorine gas. As a result the hexachlorodisilan
132	TT0042	IN	1314/KOLNP/2012	The invention relates to a method for producing hexachlorodisilane. Hexachlorodisilane is obtained by the oxidative splitting of the chlorinated polysilane of the empirical formula SiCl_x ($x = 0,2- 0,8$) using chlorine gas. As a result the hexachlorodisilan
133	TT0042	US	13/512,678	The invention relates to a method for producing hexachlorodisilane. Hexachlorodisilane is obtained by the oxidative splitting of the chlorinated polysilane of the empirical formula SiCl_x ($x = 0,2- 0,8$) using chlorine gas. As a result the hexachlorodisilan
134	TT0043	IN	1316/KOLNP/2012	The invention relates to a method and a device for producing short-chained halogenated polysilanes and/or short-chained halogenated polysilanes and halogenide-containing silicon by thermolytic decomposition of long-chained halogenated polysilanes. The the
135	TT0043	US	13/512,905	The invention relates to a method and a device for producing short-chained halogenated polysilanes and/or short-chained halogenated polysilanes and halogenide-containing silicon by thermolytic decomposition of long-chained halogenated polysilanes. The the
136	TT0044	IN	1315/KOLNP/2012	The invention relates to a chlorinated polysilane which has the formula SiCl_x wherein $x = 0,01 - 0,8$ and which can be produced in particular by the thermolysis of a chloropolysilane at a temperature below 600 DEG C.
137	TT0044	JP	5667203	The invention relates to a chlorinated polysilane which has the formula SiCl_x wherein $x = 0,01 - 0,8$ and which can be produced in particular by the thermolysis of a chloropolysilane at a temperature below 600 DEG C.
138	TT0044	US	13/512,461	The invention relates to a chlorinated polysilane which has the formula SiCl_x wherein $x = 0,01 - 0,8$ and which can be produced in particular by the thermolysis of a chloropolysilane at a temperature below 600 DEG C.
139	TT0055	CN	201180035876.4	The invention relates to the generation of hydrogen for operating fuel cells in aircraft, wherein hydrogen is generated by reacting hydrogenated polysilanes (HPS) with water in a reaction chamber. The reaction chamber comprises a feed device and a dischar
140	TT0055	DE	502011005988.4	The invention relates to the generation of hydrogen for operating fuel cells in aircraft, wherein hydrogen is generated by reacting hydrogenated polysilanes (HPS) with water in a reaction chamber. The reaction chamber comprises a feed device and a dischar
141	TT0055	FR	2596541	The invention relates to the generation of hydrogen for operating fuel cells in aircraft, wherein hydrogen is generated by reacting hydrogenated polysilanes (HPS) with water in a reaction chamber. The reaction chamber comprises a feed device and a dischar
142	TT0055	GB	2596541	The invention relates to the generation of hydrogen for operating fuel cells in aircraft, wherein hydrogen is generated by reacting hydrogenated polysilanes (HPS) with water in a reaction chamber. The reaction chamber comprises a feed device and a dischar
143	TT0055	IN	176/KOLNP/2013	The invention relates to the generation of hydrogen for operating fuel cells in aircraft, wherein hydrogen is generated by reacting hydrogenated polysilanes (HPS) with water in a reaction chamber. The reaction chamber comprises a feed device and a

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				dischar
144	TT0055	IN	176/KOLNP/2013	The invention relates to the generation of hydrogen for operating fuel cells in aircraft, wherein hydrogen is generated by reacting hydrogenated polysilanes (HPS) with water in a reaction chamber. The reaction chamber comprises a feed device and a dischar
145	TT0055	JP	2013-521072	The invention relates to the generation of hydrogen for operating fuel cells in aircraft, wherein hydrogen is generated by reacting hydrogenated polysilanes (HPS) with water in a reaction chamber. The reaction chamber comprises a feed device and a dischar
146	TT0055	KR	10-2013-7004594	The invention relates to the generation of hydrogen for operating fuel cells in aircraft, wherein hydrogen is generated by reacting hydrogenated polysilanes (HPS) with water in a reaction chamber. The reaction chamber comprises a feed device and a dischar
147	TT0055	KR	10-2013-7004594	The invention relates to the generation of hydrogen for operating fuel cells in aircraft, wherein hydrogen is generated by reacting hydrogenated polysilanes (HPS) with water in a reaction chamber. The reaction chamber comprises a feed device and a dischar
148	TT0055	US	13/811,521	The invention relates to the generation of hydrogen for operating fuel cells in aircraft, wherein hydrogen is generated by reacting hydrogenated polysilanes (HPS) with water in a reaction chamber. The reaction chamber comprises a feed device and a dischar
149	TT0047	CN	ZL201080054817.7	The present invention relates to a method for producing halogenated polysilanes as a pure compound or mixture of compounds, which has a specific purity in relation to inter alia boron-containing compounds. An embodiment of the invention is a method for pr
150	TT0047	DE	502010005346.8	The present invention relates to a method for producing halogenated polysilanes as a pure compound or mixture of compounds, which has a specific purity in relation to inter alia boron-containing compounds. An embodiment of the invention is a method for pr
151	TT0047	EP	2507174	The present invention relates to a method for producing halogenated polysilanes as a pure compound or mixture of compounds, which has a specific purity in relation to inter alia boron-containing compounds. An embodiment of the invention is a method for pr
152	TT0047	FR	2507174	The present invention relates to a method for producing halogenated polysilanes as a pure compound or mixture of compounds, which has a specific purity in relation to inter alia boron-containing compounds. An embodiment of the invention is a method for pr
153	TT0047	GB	2507174	The present invention relates to a method for producing halogenated polysilanes as a pure compound or mixture of compounds, which has a specific purity in relation to inter alia boron-containing compounds. An embodiment of the invention is a method for pr
154	TT0047	IN	1320/KOLNP/2012	The present invention relates to a method for producing halogenated polysilanes as a pure compound or mixture of compounds, which has a specific purity in relation to inter alia boron-containing compounds. An embodiment of the invention is a method for pr
155	TT0047	US	9,139,702	The present invention relates to a method for producing halogenated polysilanes as a pure compound or mixture of compounds, which has a specific purity in relation to inter alia boron-containing compounds. An embodiment of the invention is a method for pr

156	TT0029	DE	102008036143.7	The invention describes a process for removing nonmetallic impurities from metallurgical silicon. A melt is produced from metallurgical silicon and halide containing silicon. As a result, the impurities are submitted out and removed from the melt in the fo
157	TT0040	DE	102009056731.3	The invention relates to a method for producing hydrogenated polygermasilane as a pure compound or a mixture of compounds, wherein halogenated polygermasilane is hydrogenated. The invention also relates to a hydrogenated polygermasilane, to a germanium la
158	TT0040	EP	10792879.8	The invention relates to a method for producing hydrogenated polygermasilane as a pure compound or a mixture of compounds, wherein halogenated polygermasilane is hydrogenated. The invention also relates to a hydrogenated polygermasilane, to a germanium la
159	TT0041	DE	102009056731.3	The invention relatet to chlorinated oligogermanes as a pure compound or as a mixture of compounds, and to a method for the production thereof. The chlorinated oligogermanes as a pure compound or a mixture of compounds respectively comprise at least one d
160	TT0041	EP	10787451.3	The invention relatet to chlorinated oligogermanes as a pure compound or as a mixture of compounds, and to a method for the production thereof. The chlorinated oligogermanes as a pure compound or a mixture of compounds respectively comprise at least one d
161	TT0043	DE	102009056437.3	The invention relates to a method and a device for producing short chained halogenated polysilanes and/or short chaind halogenated polysilanes and halogenide containing silicon by thermolytic decomposition of long chained halogenated polysilanes. The the
162	TT0043	EP	10787414.1	The invention relates to a method and a device for producing short chained halogenated polysilanes and/or short chaind halogenated polysilanes and halogenide containing silicon by thermolytic decomposition of long chained halogenated polysilanes. The the
163	TT0048	DE	102010025710.9	The invention relatet to a storage material for obtaining H-silanes which is present in the form of a hydrogenated polysilane (HPS), as a pure compound or as a mixture of compounds having on average at least six direct Si-Si bonds, the substituents of whi.
164	TT0048	EP	11757745.2	The invention relatet to a storage material for obtaining H-silanes which is present in the form of a hydrogenated polysilane (HPS), as a pure compound or as a mixture of compounds having on average at least six direct Si-Si bonds, the substituents of whi.
165	TT0049	DE	102010025948.9	The invention relates to polysilanes of medium chain length as pure compounds or a mixture of compounds, each with at least one direct Si-Si bond, the substituents of said polysilanes consisting exclusively of halogen and/or hydrogen, the medium chain len
166	TT0049	EP	11730630.8	The invention relates to polysilanes of medium chain length as pure compounds or a mixture of compounds, each with at least one direct Si-Si bond, the substituents of said polysilanes consisting exclusively of halogen and/or hydrogen, the medium chain len
167	TT0053	DE	102010019874.9	The invention relates to nano-wires which consists of or comprise semiconductor materilas and are used for applications in photovoltaics and electronics and to a method for the production thereof. The nano wires are characerized in that they are obtained
168	TT0053	EP	11720073.3	The invention relates to nano-wires which consists of or comprise semiconductor materilas and are used for applications in photovoltaics and electronics and to a method for the production thereof. The nano wires are characerized in that they are obtained
169	TT0058	DE	102012108250.2	One embodiment of the invention concerns a method for depositing Si layers or substrates, there being deposited on a substrate in a chemical gas phase process layers of silicon from at least one precursor which is PATENT halogenosilane

				compounds of
170	TT0056	EP	13753307.1	One embodiment of the invention concerns a method for depositing Si layers on substrates, there being deposited on a substrate in a chemical gas phase process layers of silicon from at least one precursor which is selected from halogenosilane compounds of
171	TT0056	WO	PCT/EP2013/067150	One embodiment of the invention concerns a method for depositing Si layers on substrates, there being deposited on a substrate in a chemical gas phase process layers of silicon from at least one precursor which is selected from halogenosilane compounds of
172	TT0067	DE	To Be Filed	Base catalyzed formation of higher halogenated oligosilanes from hexahalogenosilanes.